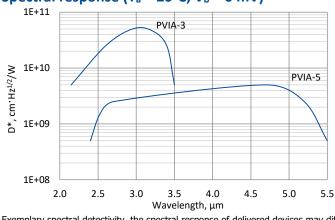


PVIA series

2.0 – 5.5 μm InAs and InAsSb ambient temperature, optically immersed photovoltaic detectors

PVIA series features uncooled IR photovoltaic detectors based on $InAs_{1-x}Sb_x$ alloys, optically immersed in order to improve performance of the devices. The detectors are temperature stable up to 300°C and mechanically durable. They do not contain mercury or cadmium and are complying with the RoHS Directive.

Spectral response ($T_a = 20$ °C, $V_b = 0$ mV)





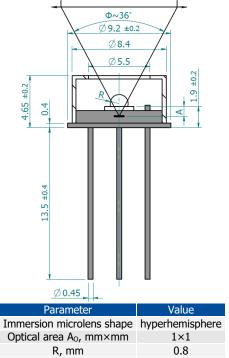
Exemplary spectral detectivity, the spectral response of delivered devices may differ.

Specification ($T_a = 20$ °C, $V_b = 0$ mV)

Parameter	Detector type	
	PVIA-3	PVIA-5
Active element material	epitaxial InAs heterostructure	epitaxial InAsSb heterostructure
Cut-on wavelength $\lambda_{\text{cut-on}}$ (10 %), μ m	2.15±0.20	2.3±0.2
Peak wavelength λ _{peak} , μm	2.95±0.30	4.7±0.3
Cut-off wavelength $\lambda_{\text{cut-off}}$ (10 %), μm	3.5±0.2	5.5±0.2
Current responsivity $R_i(\lambda_{peak})$, A/W	≥1.3	≥1.3
Detectivity D*(λ_{peak}), cm·Hz ^{1/2} /W	≥5.0×10 ¹⁰	≥5.0×10 ⁹
Time constant т, ns	≤20	≤15
Resistance R, Ω	≥2k	≥70
Optical area A _o , mm×mm	1×1	
Package	TO39	
Acceptance angle Φ	~36°	
Window	none	







A, mm

Φ – acceptance angle
R – hyperhemisphere microlens radius
A – distance from the bottom of hyperhemisphere microlens to the focal plane

2.4±0.2

Dedicated preamplifier



small SIP-TO39

